

PUMX2

NPN/NPN general-purpose double transistors

Rev. 02 — 17 November 2009

Product data sheet

1. Product profile

1.1 General description

NPN/NPN general-purpose double transistors in a small SOT363 (SC-88) Surface Mounted Device (SMD) plastic package.

1.2 Features

- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

1.3 Applications

General-purpose switching and amplification

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	tor					
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I _C	collector current		-	-	150	mA
h _{FE}	DC current gain	$V_{CE} = 6 \text{ V}; I_{C} = 1 \text{ mA}$	120	250	560	

2. Pinning information

Table 2. Pinning

	9		
Pin	Description	Simplified outline	Symbol
1	emitter TR1		
2	emitter TR2	654	6 5 4
3	base TR2		TR1 TR2
4	collector TR2	0	
5	base TR1	□1 □2 □3	1 2 3
6	collector TR1		006aaa653



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Ordering information

Table 3. **Ordering information**

Type number	Package		
	Name	Description	Version
PUMX2	SC-88	plastic surface mounted package; 6 leads	SOT363

Marking 4.

Table 4. **Marking codes**

Type number	Marking code ^[1]
PUMX2	Z1*

^{[1] * = -:} made in Hong Kong

Limiting values

Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit		
Per transist	Per transistor						
V_{CBO}	collector-base voltage	open emitter	-	60	V		
V_{CEO}	collector-emitter voltage	open base	-	50	V		
V_{EBO}	emitter-base voltage	open collector	-	7	V		
I _C	collector current		-	150	mA		
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA		
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA		
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	180	mW		
Per device							
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	300	mW		
T _{stg}	storage temperature		-65	+150	°C		
T _j	junction temperature		-	150	°C		
T _{amb}	ambient temperature		-65	+150	°C		

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

Thermal characteristics

Table 6. **Thermal characteristics**

Parameter	Conditions	Min	Тур	Max	Unit
istor					
thermal resistance from junction to ambient	in free air	[1] -	-	694	K/W
е					
thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	417	K/W
	thermal resistance from junction to ambient e thermal resistance from	thermal resistance from in free air junction to ambient e thermal resistance from in free air	thermal resistance from in free air in free air junction to ambient e thermal resistance from in free air in free	thermal resistance from in free air in fre	thermal resistance from in free air in fre

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

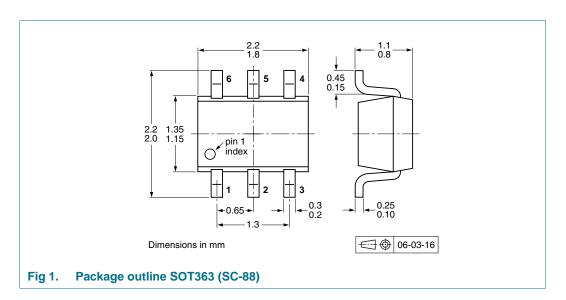
Table 7. **Characteristics**

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
I _{CBO}	collector-base	$V_{CB} = 60 \text{ V}; I_{E} = 0 \text{ A}$	-	-	100	nA
	cut-off current	$V_{CB} = 60 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 7 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 6 \text{ V}; I_{C} = 1 \text{ mA}$	120	250	560	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	-	-	250	mV
f _T	transition frequency	$V_{CE} = 12 \text{ V}; I_{E} = 2 \text{ mA};$ f = 100 MHz	100	-	-	MHz
C _c	collector capacitance	$V_{CB} = 12 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF

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Package outline



Packing information 9.

Table 8. **Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

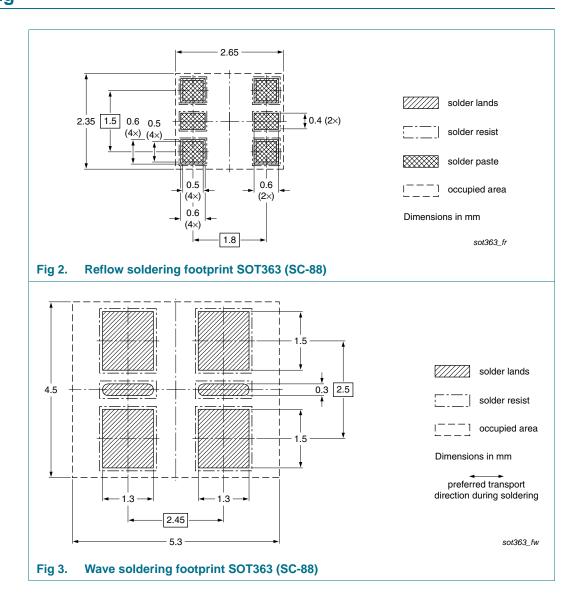
Type number	Package	Description		Packing qua	antity
				3000	10000
PUMX2	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-165

^[1] For further information and the availability of packing methods, see Section 13.

T1: normal taping

T2: reverse taping

10. Soldering



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11. Revision history

Table 9. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PUMX2_2	20091117	Product data sheet	-	PUMX2_1
Modifications:		eet was changed to reflect w legal definitions and discl		
	Figure 1 "Pad	ckage outline SOT363 (SC	<u>-88)"</u> : updated	
	Figure 2 "Ref	flow soldering footprint SO	T363 (SC-88)": updated	
	• Figure 3 "Wa	ive soldering footprint SOT	363 (SC-88)": updated	
PUMX2_1	20051110	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Product data sheet

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Date of release: 17 November 2009 Document identifier: PUMX2_2

